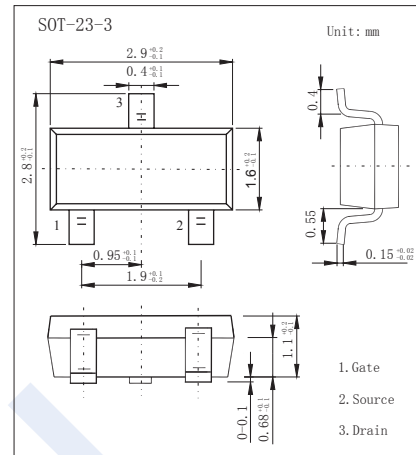


## P-Channel Enhancement MOSFET

## KI001P

## ■ Features

- $V_{DS} (V) = -12V$
- $I_D = -2.8 A$
- $R_{DS(ON)} < 100m\Omega$  ( $V_{GS} = -4.5V$ )
- $R_{DS(ON)} < 150m\Omega$  ( $V_{GS} = -2.5V$ )

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-12	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	
Continuous Drain Current	$I_D$	-2.8	A
Power Dissipation	$P_D$	1.2	W
Junction Temperature	$T_J$	150	$^\circ C$
Junction and Storage Temperature Range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D = -250 \mu A, V_{GS} = 0V$	-12	-18		V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -12V, V_{GS} = 0V, T_J = 25^\circ C$			1	$\mu A$
Gate-Body leakage current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 12V$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4	-0.7	-1.1	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -1A$			100	m $\Omega$
		$V_{GS} = -2.5V, I_D = -0.5A$			150	